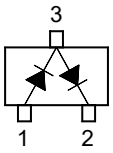
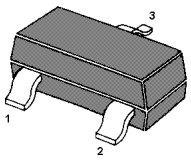
BAV99-AH

Silicon Epitaxial Planar Switching Diode

Fast switching in thick and thin-film circuits diode





Marking Code: **A7**
TO-236 Plastic Package

Features

- AEC-Q101 Qualified
- Halogen and Antimony Free(HAF), RoHS compliant

Absolute Maximum Ratings (T_a = 25℃)

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	100	V
Continuous Reverse Voltage		V_R	100	V
Continuous Forward Current (Double Diode Loaded)		I_F	125	mA
Continuous Forward Current (Single Diode Loaded)		I_F	215	mA
Repetitive Peak Forward Current		I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s at t = 1 ms at t = 1 µs	I_{FSM}	0.5 1 4.5	A
Power Dissipation		P_{tot}	350	mW
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	- 65 to + 150	℃

Characteristics at T_a = 25℃

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 150 mA	V_F	 0.715 0.855 1 1.25	V
Reverse Current at V_R = 25 V at V_R = 75 V at V_R = 25 V, T_j = 150℃ at V_R = 75 V, T_j = 150℃	I_R	 30 1 30 50	 nA µA µA µA
Total Capacitance at V_R = 0 , f = 1 MHz	C_T	1.5	pF
Reverse Recovery Time at I_{rr} = 0.1 × I_R, I_F = 10 mA, V_R = 6 V, R_L = 100 Ω	t_{rr}	4	ns

Dated: 17/06/2020 SLB3 Rev: 03

Electrical Characteristics Curves

Fig 1. Power Dissipation vs Ambient Temperature

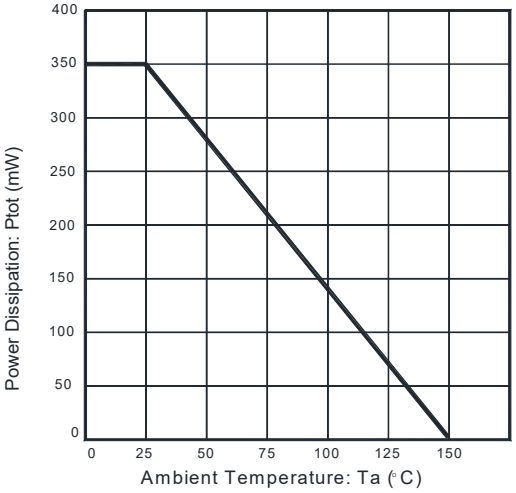


Fig 2. Total Capacitance vs. Reverse Voltage

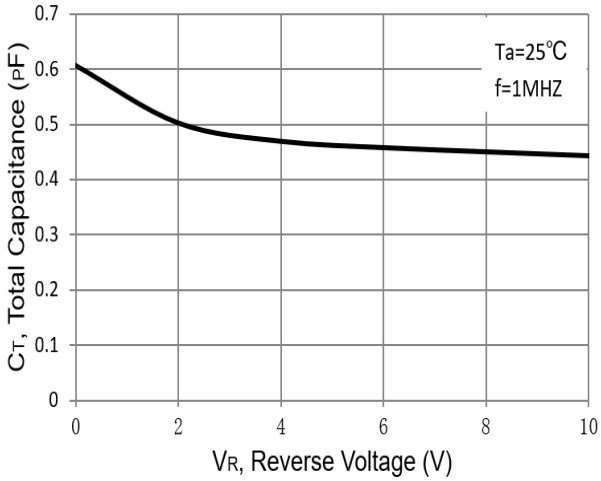


Fig 3. Reverse Current vs. Reverse Voltage

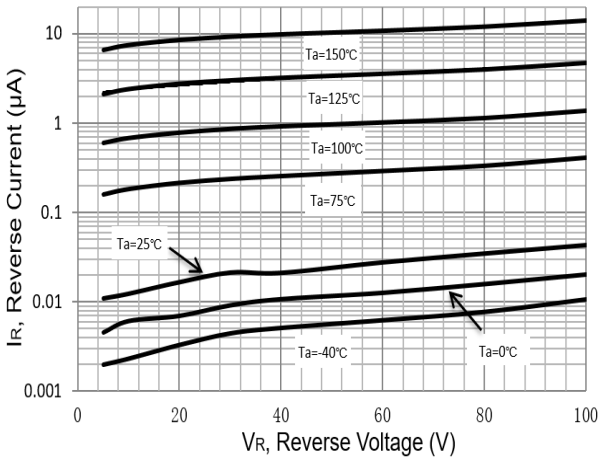
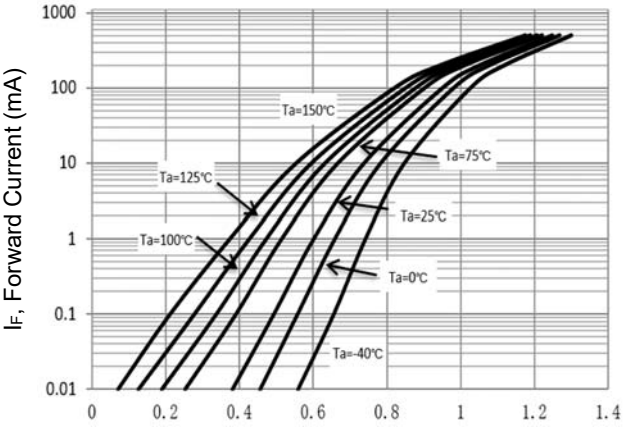
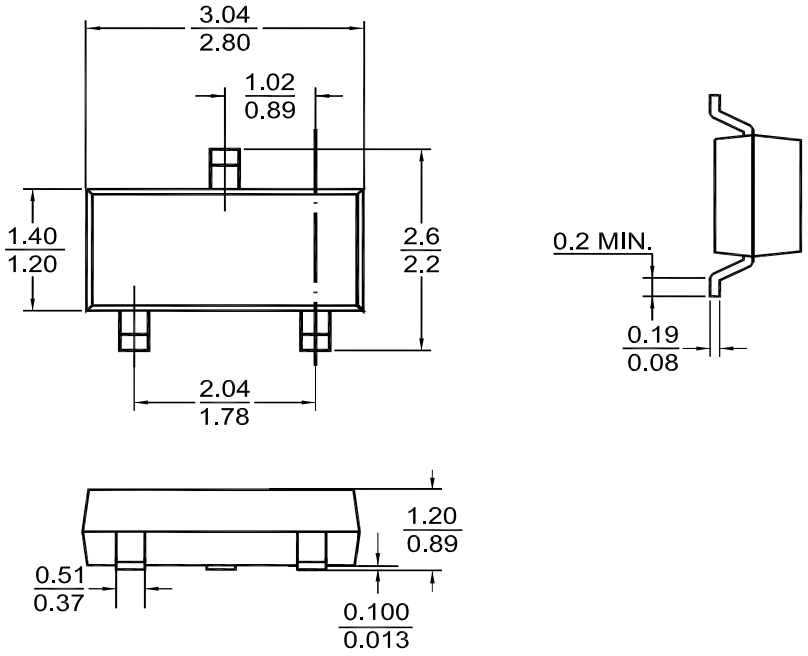


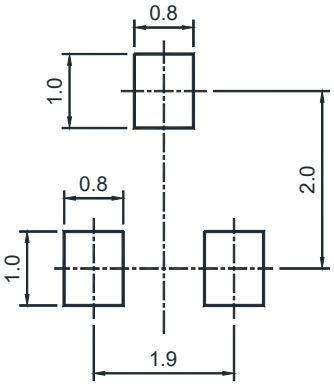
Fig 4. Forward Characteristics



Package Outline (Dimensions in mm) TO-236



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" A7 " = Part No.
" • " = HAF (Halogen and Antimony Free)
" YM " = Date Code Marking
" Y " = Year
" M " = Month
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